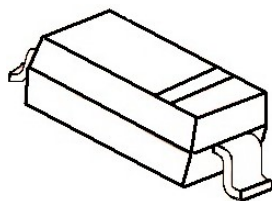


SOD-123



SOD-123 贴片塑封稳压二极管

SOD-123 Plastic-Encapsulate Zener Diode

特征 Features

- 齐纳击穿阻抗低; Low Zener Impedance
- 最大功率耗散 500mW; Power Dissipation of 500mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOD-123 封装 SOD-123 Small Outline Plastic Package
- 极性: 色环端为负极 Polarity: Color band denotes cathode end
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
功率消耗 Power Dissipation	Pd	500 ¹⁾	mW
正向压降 Forward Voltage @IF=10mA	Vf	0.9 ²⁾	V
存储温度 Storage temperature range	Ts	-65-+150	°C
Thermal resistance junction to ambient air Warmewiderstand Sperrschicht -umgebende Luft	RthA	400	K/W ¹⁾

1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²

2) Short duration test pulse used to minimize self-heating effect

3) f=1KHz

电特性 (TA = 25°C 除非另有规定)

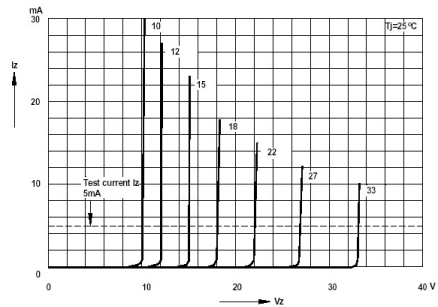
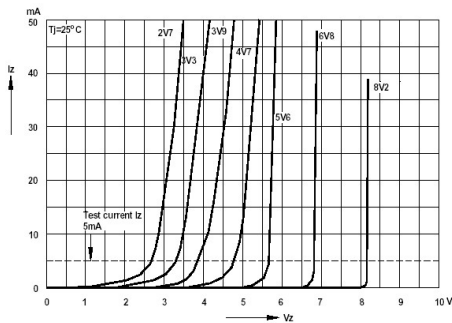
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Device	Marking	Zener Voltage Range				Maximum Zener Impedance ³⁾			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω			mA	uA			V
BZT52C2V0	WY	2.0	1.80	2.15	5	150	600	1.0	100	1.0	-3.5	0	5
BZT52C2V4	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5

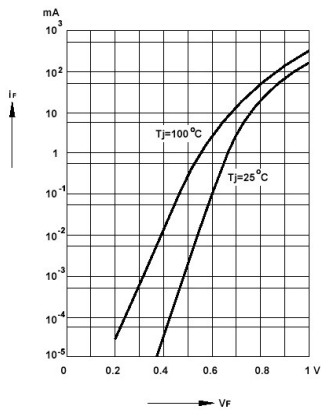
BZT52C Series

Device	Marking	Zener Voltage Range				Maximum Zener Impedance			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR			
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V	Min	Max	mA
BZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43	WU	43	40.0	46.0	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52C47	WV	47	44.0	50.0	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52C51	WW	51	48.0	54.0	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52C56	XW	56	52.0	60.0	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52C62	6E	62	58.0	66.0	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52C68	6F	68	64.0	72.0	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52C75	6H	75	70.0	79.0	2	300	1000	1.0	0.2	57	10.0	12.0	5

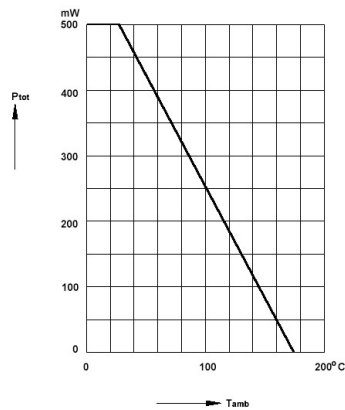
Breakdown characteristics
at Tj=constant (pulsed)



Forward characteristics

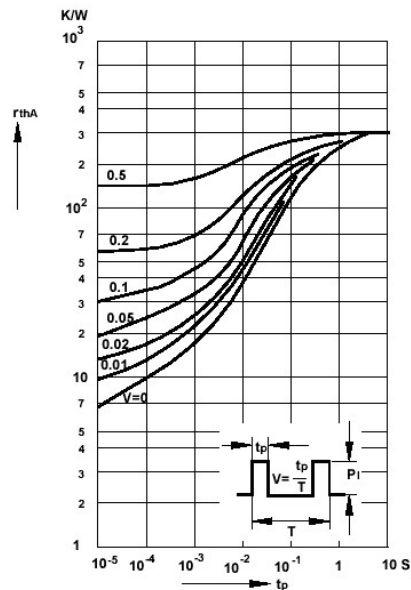


Admissible power dissipation versus ambient temperature

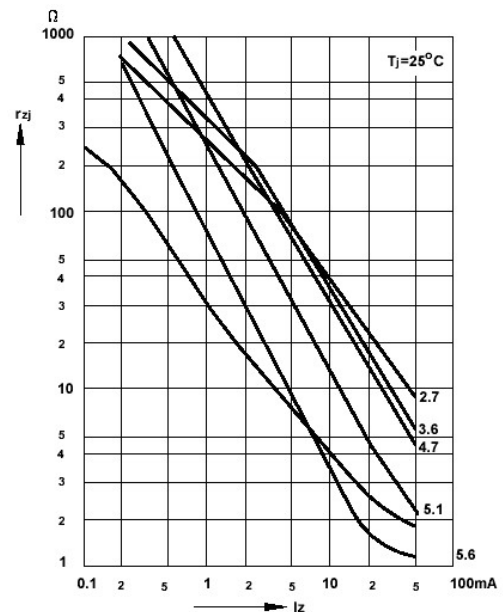


BZT52C Series

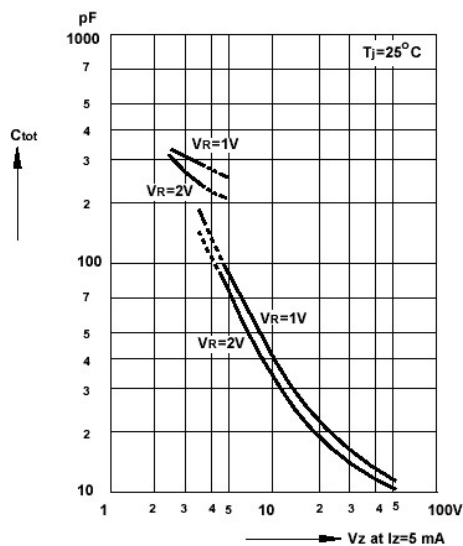
Pulse thermal resistance versus pulse duration



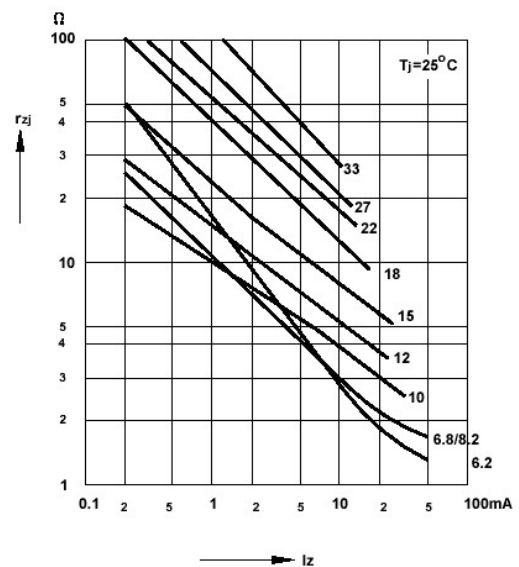
Dynamic resistance versus Zener current



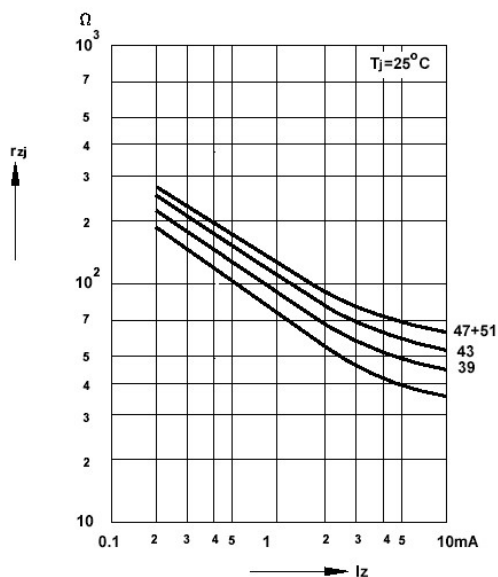
Capacitance versus Zener voltage



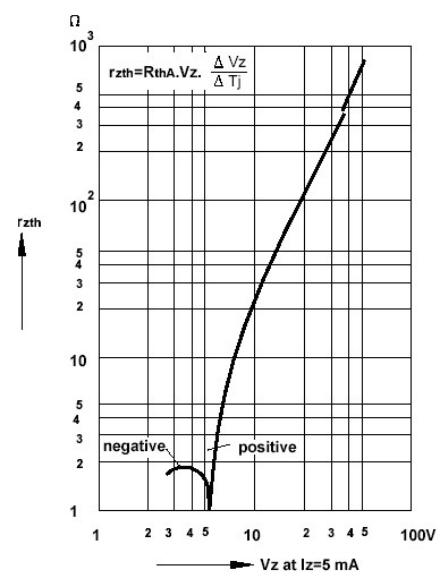
Dynamic resistance versus Zener current



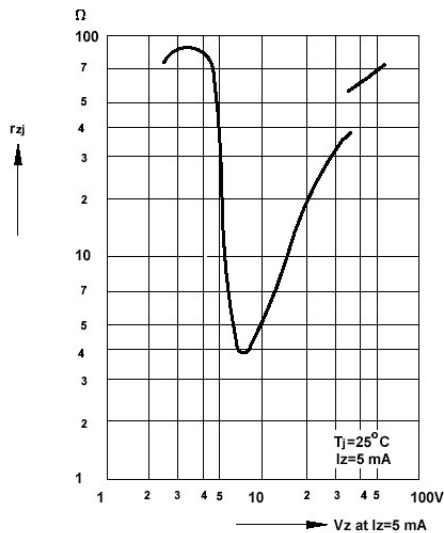
Dynamic resistance versus Zener current



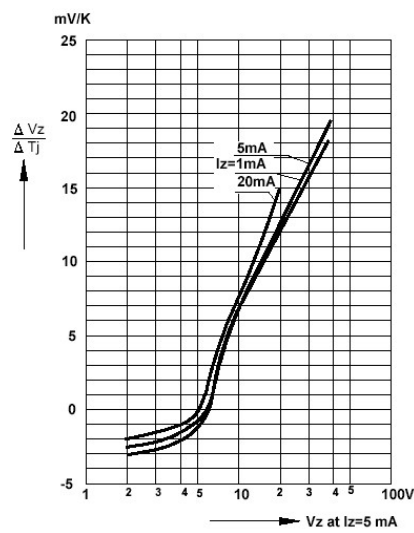
Thermal differential resistance versus Zener voltage



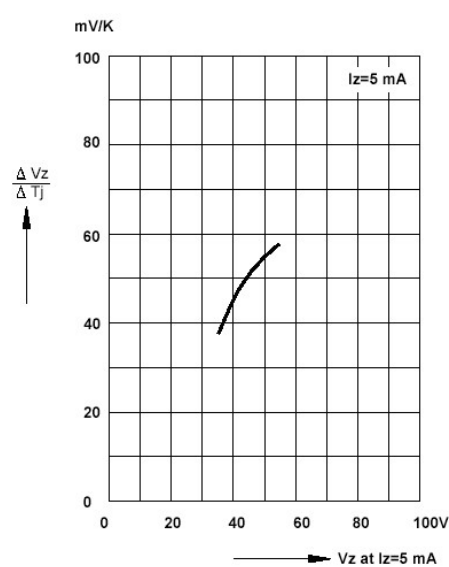
Dynamic resistance versus Zener voltage



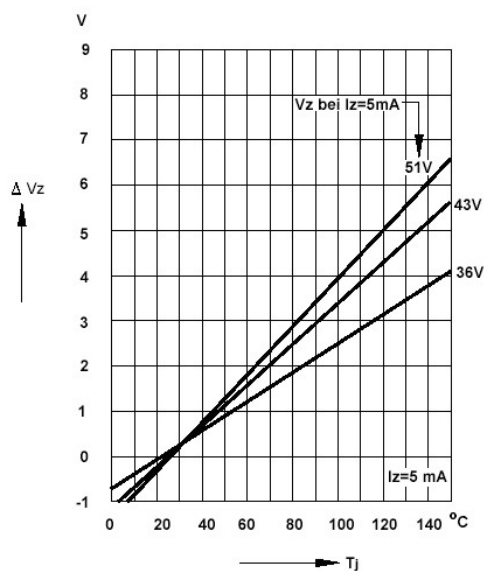
Temperature dependence of Zener voltage versus Zener voltage



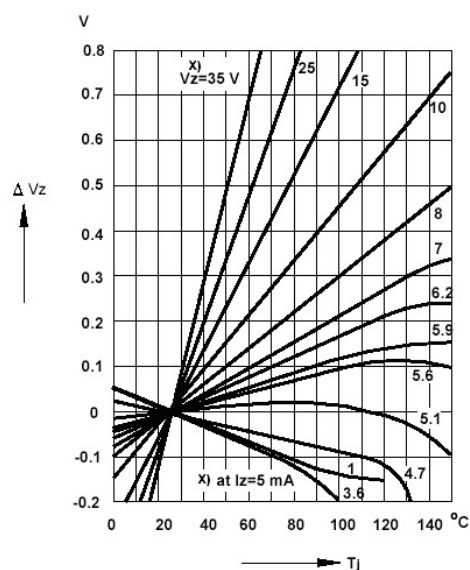
Temperature dependence of Zener voltage versus Zener voltage



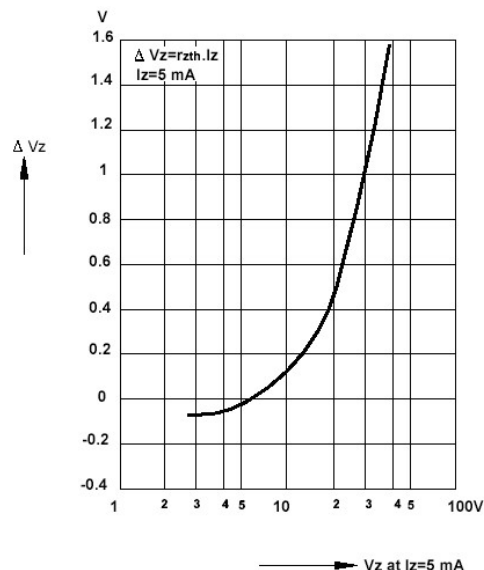
Change of Zener voltage versus junction temperature

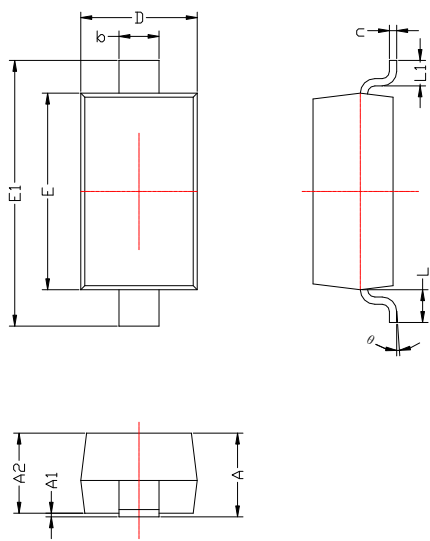


Change of Zener voltage versus junction temperature



Change of Zener voltage from turn-on up to the point of thermal equilibrium versus Zener voltage

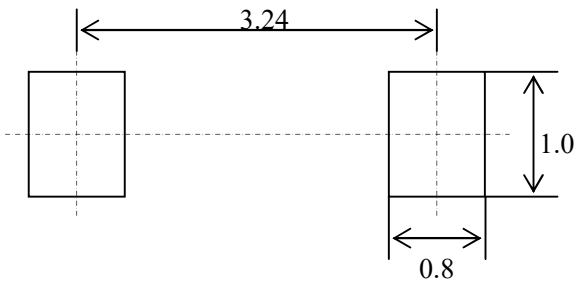




SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.450	0.650
c	0.080	0.150
D	1.500	1.700
E	2.600	2.800
E1	3.550	3.850
L	0.500REF	
L1	0.250	0.450
θ	0°	8°

焊盘设计参考

Precautions: PCB Design
Recommended land dimensions for SOD-123 diode. Electrode patterns for PCBs



中心距: 3.24
脚 宽: 0.55
焊盘宽: 1.00
脚 长: 0.50
焊盘长: 0.80

技术要求:
1, 塑封体尺寸: 2.70 X 1.60
2: 未注公差为: ±0.05
3, 所有单位: mm